

### Abstract of the Disclosure

To provide a semiconductor storage apparatus and a manufacturing method thereof in which a memory cell source area is not silicided and a resistance dispersion caused by insufficient silicidation is therefore eliminated, and in which a silicide film is prevented from being formed in the step portion of a self-aligned source structure and therefore a resistance dispersion by a disconnected silicide film is not generated. In a semiconductor storage apparatus having a memory cell portion in which a source area is formed by a self-aligned process, a silicide blocking portion is disposed in a part of the surface of a source diffusion layer such that the resistance dispersion caused by the insufficient silicidation of the source diffusion layer is not generated.